



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-123 Plastic-Encapsulate Diodes

SD103AW-SD103CW SCHOTTKY DIODES

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance

MARKING: SD103AW: S4
SD103BW: S5
SD103CW: S6



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	SD103AW	SD103BW	SD103CW	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}				
Working Peak	V _{RWM}	40	30	20	V
DC Blocking Voltage	V _R				
RMS Reverse Voltage	V _{R(RMS)}	28	21	14	V
Forward Continuous Current	I _{FM}	350			mA
Repetitive Peak Forward Current @t≤1.0s	I _{FRM}	1.5			A
Power Dissipation	P _d	400			mW
Thermal Resistance Junction to Ambient	R _{θJA}	300			°C/W
Storage temperature	T _{STG}	-65~+125			°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	SD103AW SD103BW SD103CW	40 30 20			V	IR=10μA IR=10μA IR=10μA
Forward voltage	V _F			0.37 0.60	V	I _F =20mA I _F =200mA
Reverse current	SD103AW SD103BW SD103CW			5.0	μA	V _R =30V V _R =20V V _R =10V
Capacitance between terminals	C _T		50		pF	V _R =0V, f=1.0MHz
Reverse Recovery Time	t _{rr}		10		ns	I _F =I _R =200mA I _{rr} =0.1X I _R , R _L =100Ω

Typical Characteristics

SD103AW-SD103CW

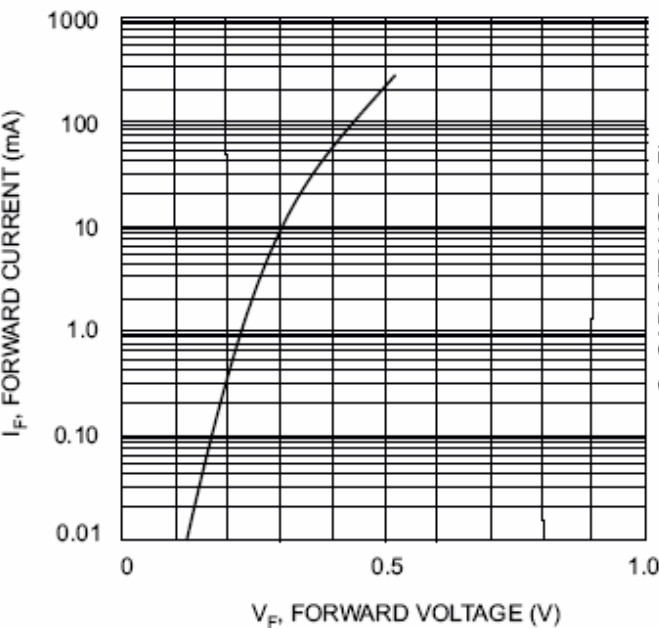


Fig. 1 Typical Forward Characteristics

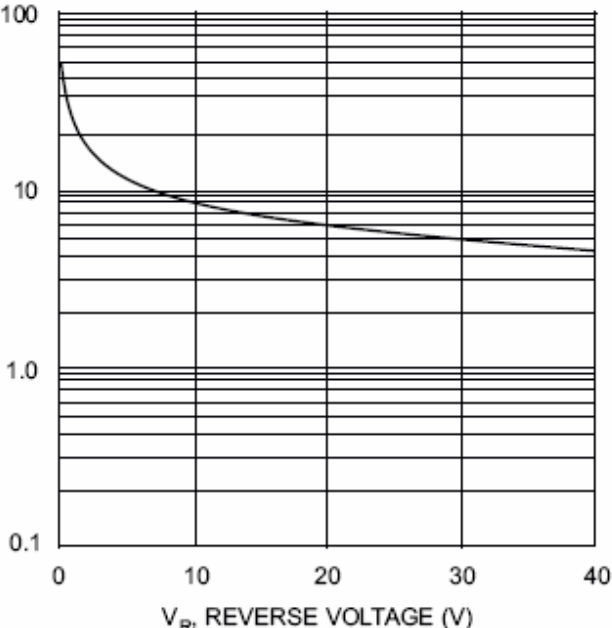


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage